



RATINGS AND CHARACTERISTIC CURVES

MOSFET ELECTRICAL CHARACTERISTICS $T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 10\mu A$	20			V
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 50\mu A$	0.65	0.95	1.2	
Gate-body leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μA
Drain-source on-resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5V, I_D = 3.6A$		0.045	0.060	Ω
		$V_{GS} = 2.5V, I_D = 3.1A$		0.070	0.115	
Forward transconductance ^a	g_{fs}	$V_{DS} = 5V, I_D = 3.6A$		8		S
Diode forward voltage	V_{SD}	$I_S = 0.94A, V_{GS} = 0V$		0.76	1.2	V
Dynamic						
Total gate charge	Q_g	$V_{DS} = 10V, V_{GS} = 4.5V, I_D = 3.6A$		4.0	10	nC
Gate-source charge	Q_{gs}			0.65		
Gate-drain charge	Q_{gd}			1.5		
Input capacitance ^b	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		300		pF
Output capacitance ^b	C_{oss}			120		
Reverse transfer capacitance ^b	C_{rss}			80		
Switching^b						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 10V,$ $R_L = 5.5\Omega, I_D \approx 3.6A,$ $V_{GEN} = 4.5V, R_g = 6\Omega$		7	15	ns
Rise time	t_r			55	80	
Turn-off delay time	$t_{d(off)}$			16	60	
Fall time	t_f			10	25	

Notes :

- a. Pulse Test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- b. These parameters have no way to verify.

MARKING: S2

Typical Characteristics

